

# **Product Specification**

## XBLW APM4953

Dual P-Channel Enhancement Mode MOSFET

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## Description

The APM4953 uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

## **General Features**

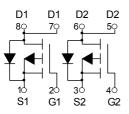
- ➢ VDS = -30V,ID = -5.3A
- ➢ RDS(ON) < 42mΩ@ VGS=-10V</p>
- > RDS(ON) < 85mΩ@ VGS=-4.5V</p>

**Package Marking and Ordering Information** 

## Application

- > PWM application
- Load switch





#### Dual P-Channel MOSFET

Package Type	Marking	Packing	Packing Qty
SOP-8	APM4953	Таре	3000Pcs/Reel

## Absolute Maximum Ratings (TA=25°Cunless otherwise noted)

Symbol	Parameter	Limit	Unit
Vds	Drain-Source Voltage	-30	V
Vgs	Gate-Source Voltage	±20	V
lo	Drain Current-Continuous	-5.3	A
Ідм	Drain Current-Pulsed (Note 1)	-20	A
PD	Maximum Power Dissipation	2.6	W
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	49	°C <b>/W</b>



## Electrical Characteristics TA=25°Cunless otherwise noted

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics		1				
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250µA	-30	-33	-	V
Zero Gate Voltage Drain Current	loss	V <sub>DS</sub> =-24V,V <sub>GS</sub> =0V	-	-	-1	μA
Gate-Body Leakage Current	lgss	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250µA	-1	-1.6	-3	V
		V <sub>GS</sub> =-10V, I <sub>D</sub> =-5.3A	-	35	42	m
Drain-Source On-State Resistance	RDS(ON)	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4.2A	-	70	85	m
Forward Transconductance	grs	V <sub>DS</sub> =-15V, I <sub>D</sub> =-4.5A	4	7	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	Clss	V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V,	-	540	-	PF
Output Capacitance	Coss		-	150	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	75	-	PF
Switching Characteristics (Note 4)	I	-				
Turn-on Delay Time	td(on)		-	8	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =-15V, ID=-1A, V <sub>GS</sub> =-10V,R <sub>GEN</sub> =6	-	14	-	nS
Turn-Off Delay Time	td(off)		-	18	-	nS
Turn-Off Fall Time	tr		-	10	-	nS
Total Gate Charge	Qg		-	12	-	nC
Gate-Source Charge	Qgs	V <sub>DS</sub> =-15V,I <sub>D</sub> =-5.3A,V <sub>GS</sub> =- 10V	-	2.4	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	3.2	-	nC
Drain-Source Diode Characteristics	1					
Diode Forward Voltage (Note 3)	Vsd	V <sub>GS</sub> =0V,I <sub>S</sub> =-5.3A	-	_	-1.2	V

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

**2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.

**3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

 $\textbf{4.} \ \textbf{Guaranteed by design, not subject to production}$ 



## **XBLW** APM4953

90%

10%

90%

50%

**Dual P-Channel Enhancement Mode MOSFET** 

<del>.</del> 50%

10%

50%

t<sub>d(off)</sub>

**INVERTED** 

**PULSE WIDTH** 

Figure 2:Switching Waveforms

t<sub>d(on)</sub>

V<sub>OUT</sub>

V<sub>IN</sub>

10%

## **Typical Electrical and Thermal Characteristics**

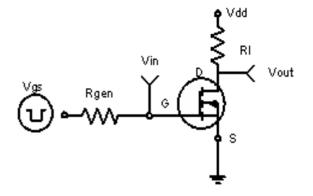
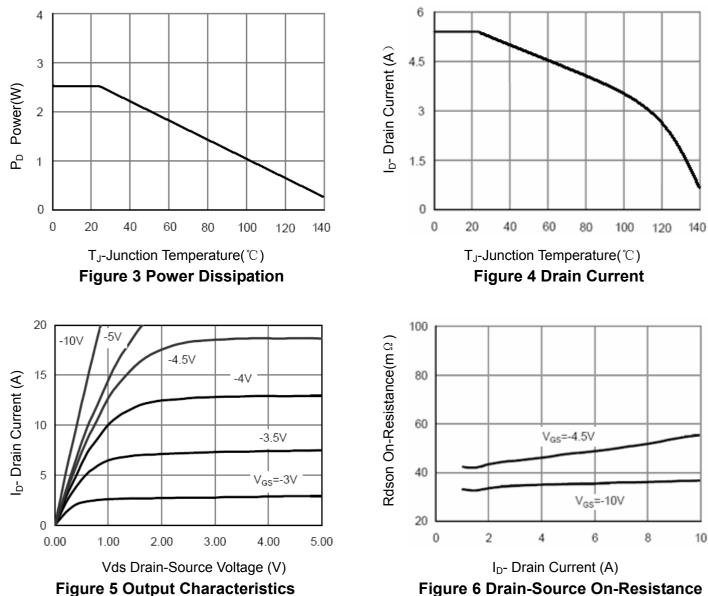
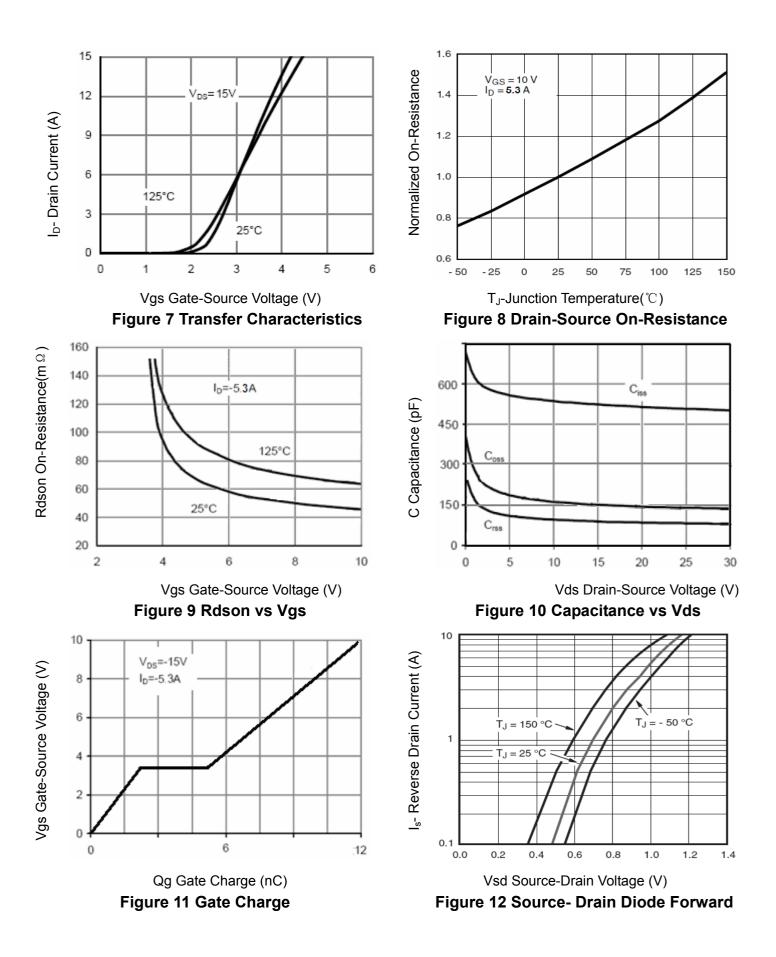


Figure 1:Switching Test Circuit





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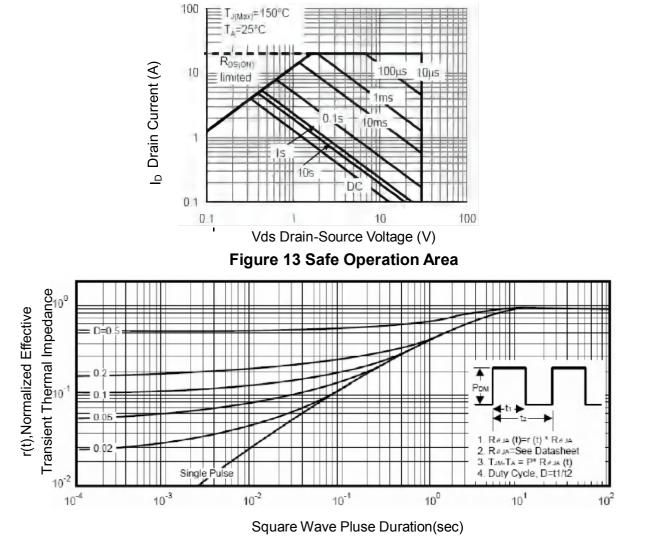


Figure 14 Normalized Maximum Transient Thermal Impedance

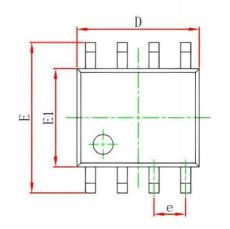


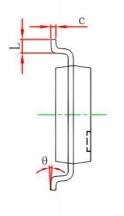
## XBLW APM4953

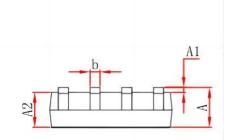
Dual P-Channel Enhancement Mode MOSFET

## **Package Outline Dimensions**

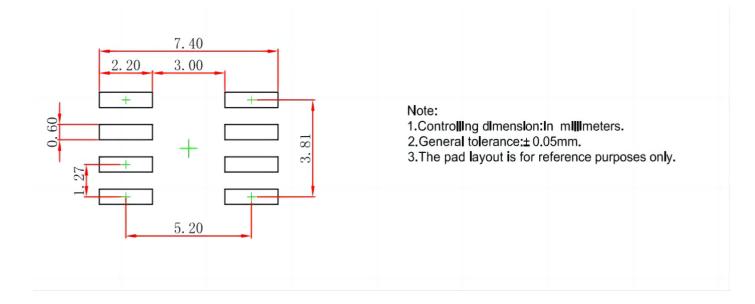
SOP-8







Symbol	Dimensions In Millimeters		Dimensions In Inches	
Symbol	Min	Max	Min	Max
А	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
с	0.170	0.250	0.007	0.010
D	4.800	5.000	0.189	0.197
е	1.270 (BSC)		0.050 (BSC)	
E	5.800	6.200	0.228	0.244
E1	3.800	4.000	0.150	0.157
L	0.400	1.270	0.016	0.050
θ	0°	8°	0 °	8°





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